

CLAIMS

1. For semiconductor manufacturing equipment, a ceramic susceptor having a resistive heating element on a surface of or inside a ceramic substrate,
5 the ceramic susceptor for semiconductor manufacturing equipment characterized in that the difference between a maximum outer diameter and a minimum outer diameter along the susceptor thickness is 0.8% or less of the average outer diameter along the susceptor wafer-support side when not heating.

10 2. A ceramic susceptor for semiconductor manufacturing equipment as set forth in claim 1, characterized in that the ceramic substrate is made of at least one ceramic selected from aluminum nitride, silicon nitride, aluminum oxynitride, and silicon carbide.

15 3. A ceramic susceptor for semiconductor manufacturing equipment as set forth in claim 1 or 2, characterized in that the resistive heating element is made from at least one metal selected from tungsten, molybdenum, platinum, palladium, silver, nickel, and chrome.

20 4. A ceramic susceptor for semiconductor manufacturing equipment as set forth in any of claims 1 through 3, characterized in that a plasma electrode is further disposed on a surface of or inside the ceramic substrate.